

# R2R Manufacturing of WOLED Lighting

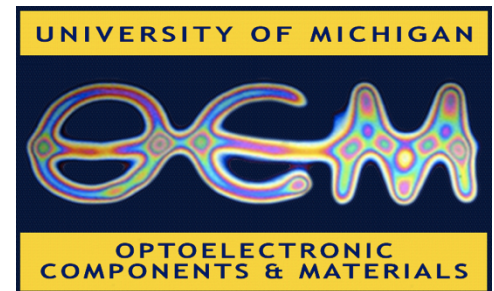
## -Methods-Results-Costs-

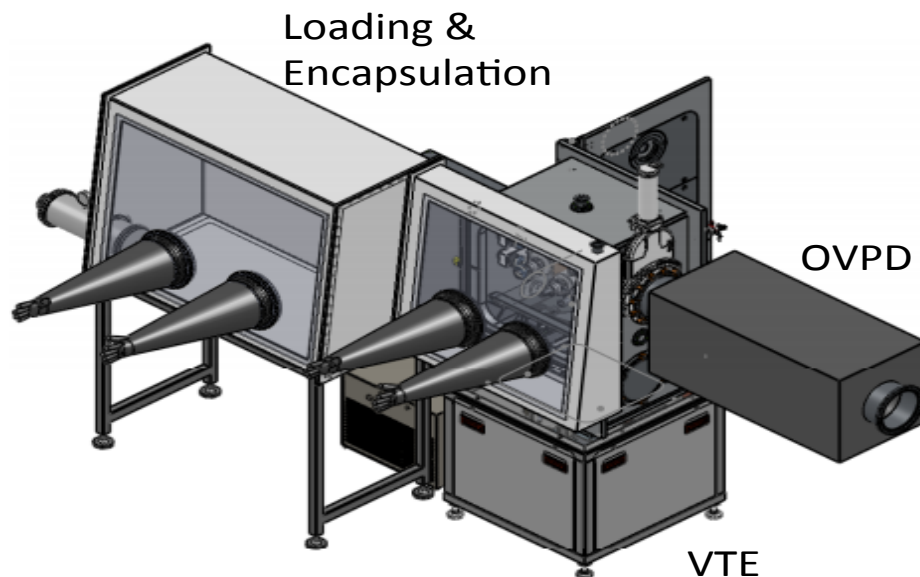
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## Prototype device fabrication system

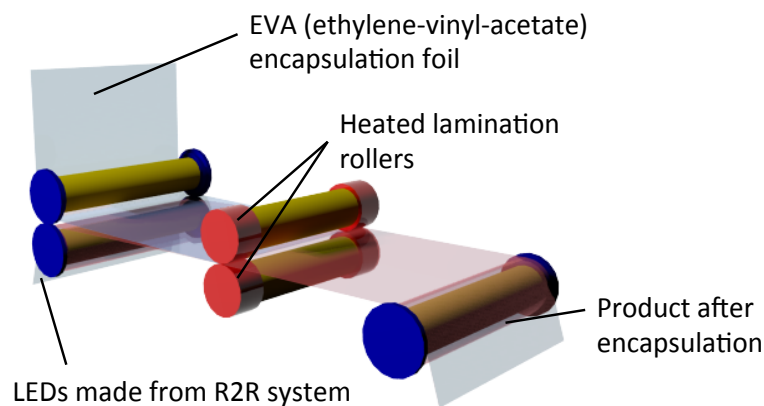
- Understand limitations
- Test Assumptions
- Use for cost basis in scale-up

## Computer Control



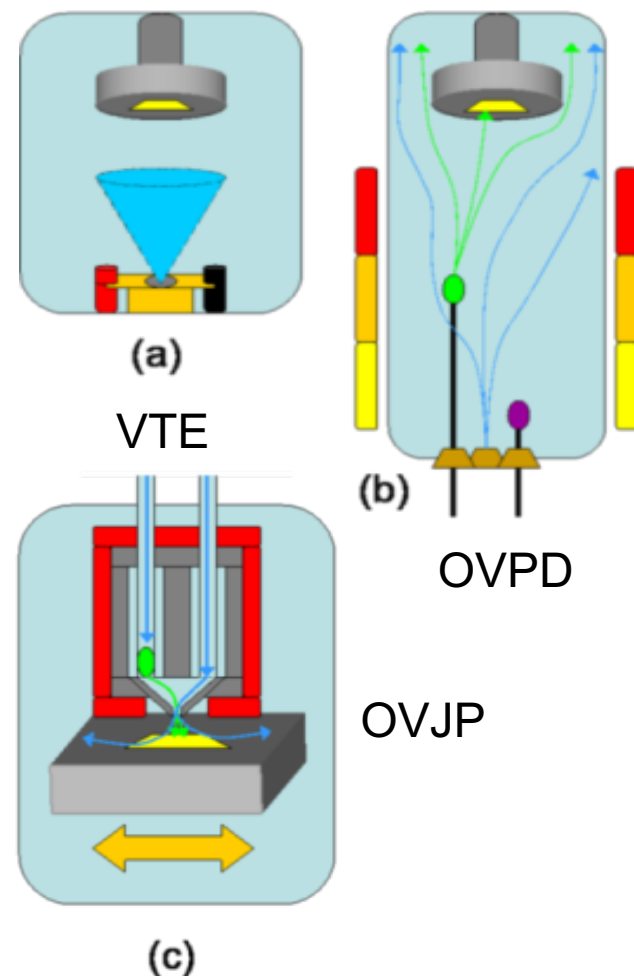
- Combination of VTE and OVPD growth
- In-situ mask patterning, registration to  $<0.1$  mm
- 10 materials sources (metals and organics)

## Future encapsulation



	Vapor (PVD)	Condensed Phase
<b>Examples</b>	VTE OVPD OVJP	Inkjet Nozzle Printing LITI $\mu$ -contact printing
<b>Materials</b>	Small molecules	Small molecules or polymers
<b>Multilayer Structures</b>	Molecularly sharp interfaces Even Mixing	Less thickness ctrl. May damage heterojunctions & complicate doping.
<b>Co-deposition</b>	Amorphous film	
<b>Patterning</b>	Thin Metal Mask Direct Print	Direct Print
<b>Atmosphere</b>	Vacuum	Inert Gas
<b>Media</b>	None	Solvent or xfer film
<b>Use</b>	Commercial & Research	Research

## Organic PVD

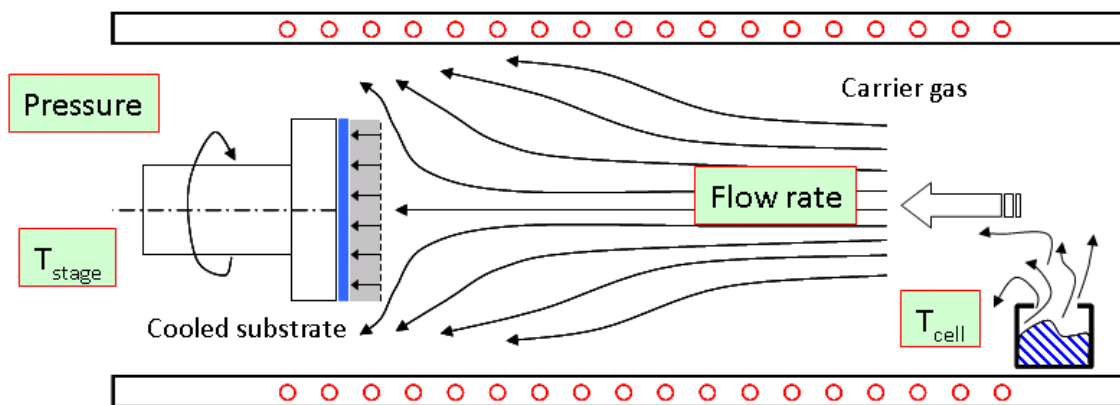


Shtein et al. *J. Appl. Phys.*  
**93**, 7, 4005 (2003)

# M Organic Vapor Phase Deposition: Concept

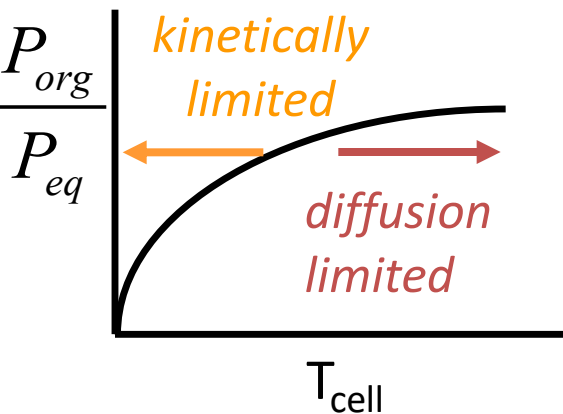
0.1 - 10 Torr

Hot wall chamber

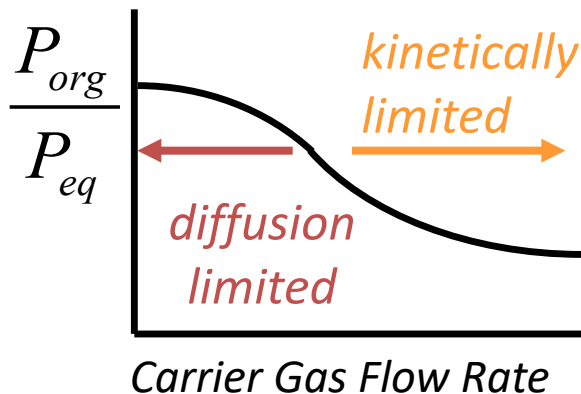


- Controlled and accurate doping  
**(gas saturated with organics - equilibrium)**
- Dust free chamber
- Efficient materials use
- Control of film crystal structure
- Very high, controlled deposition rates

Constant Flow Rate



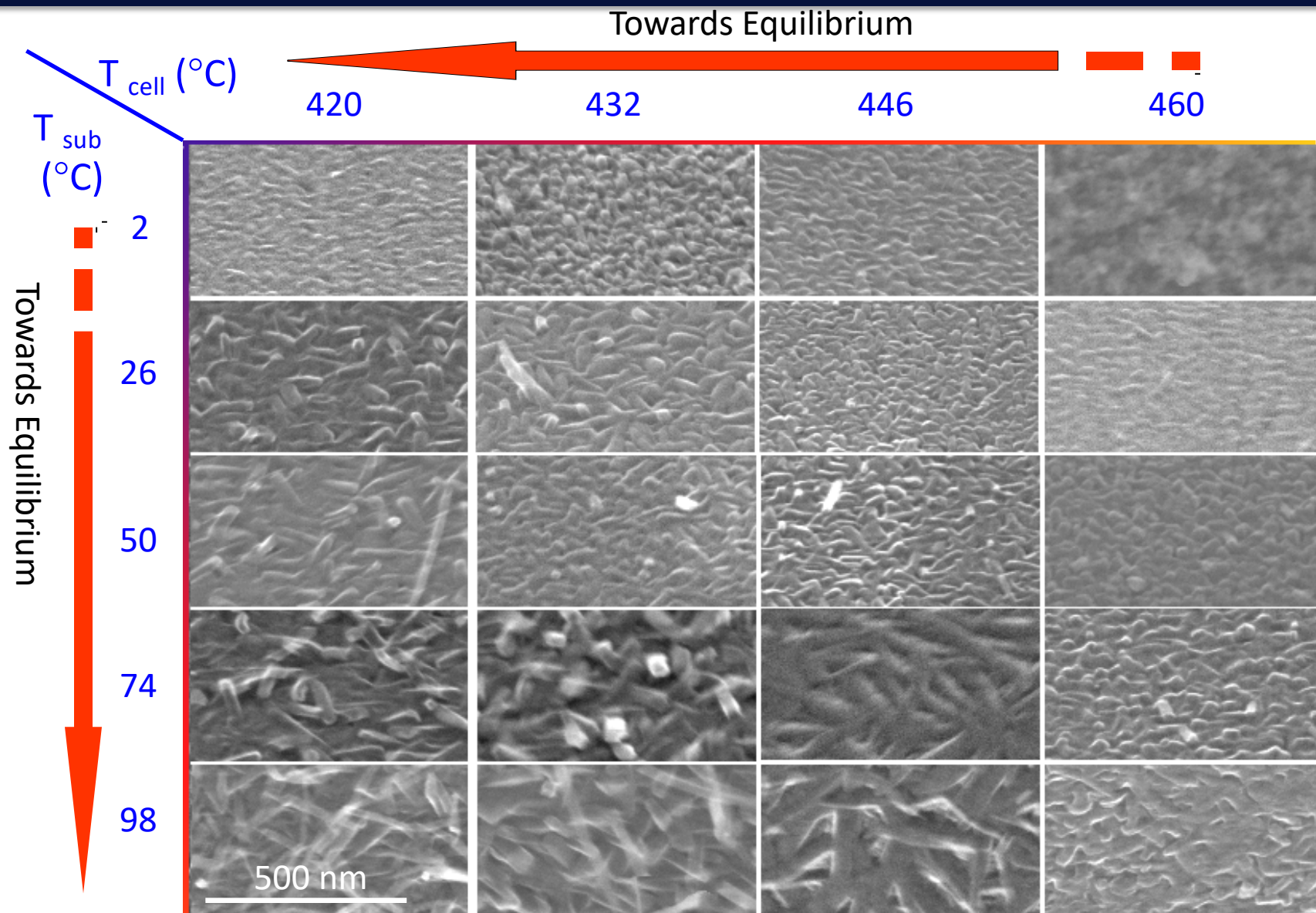
Constant Temperature



$$r_{out} = \frac{\dot{V}_{src}}{RT_{cell}} \cdot \frac{P_0 \exp(-\Delta H / RT_{cell})}{1 + \dot{V}_{src} / A_{evap} \cdot k}$$



# Nanomorphology control by temperature



(flowrate = constant, pressure = constant)



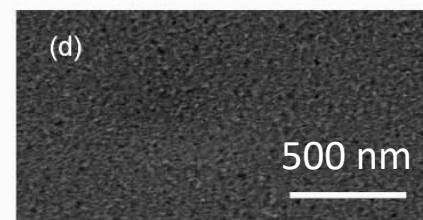
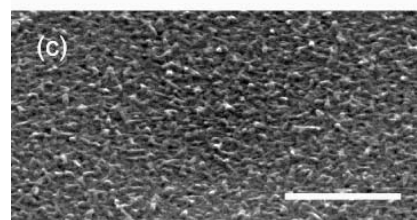
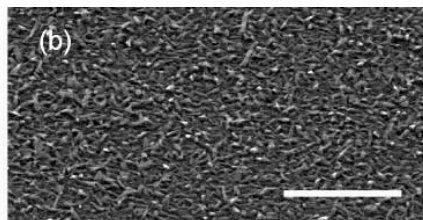
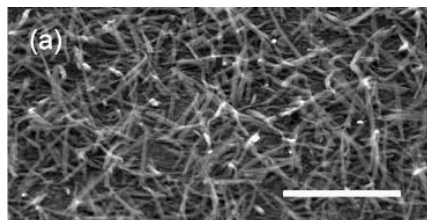
(fixed source and substrate temperatures)

N<sub>2</sub> flow rate: 100 sccm

125 sccm

150 sccm

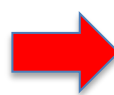
200 sccm



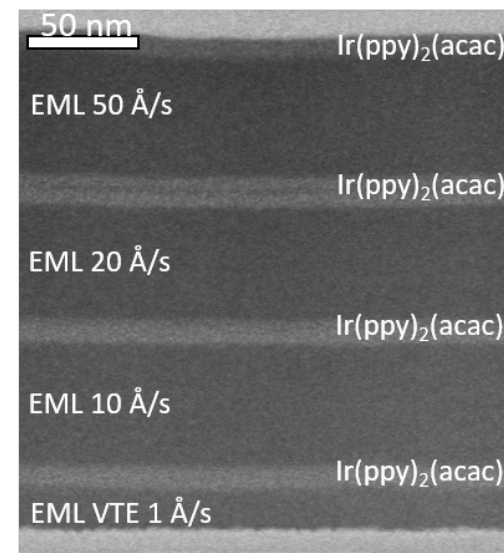
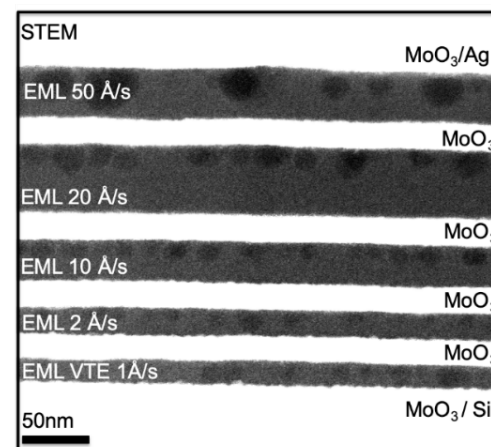
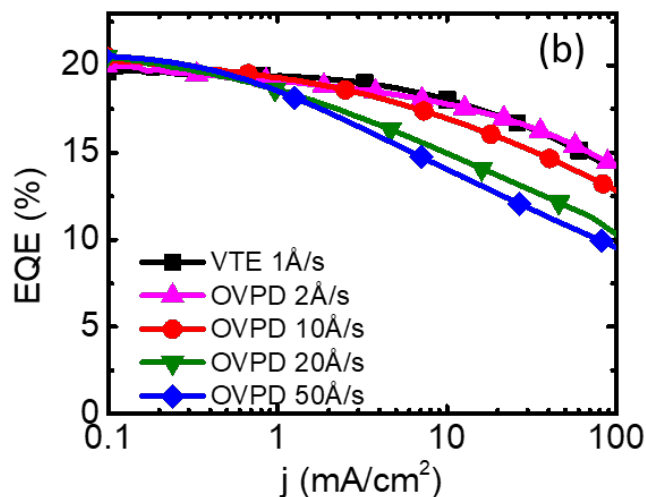
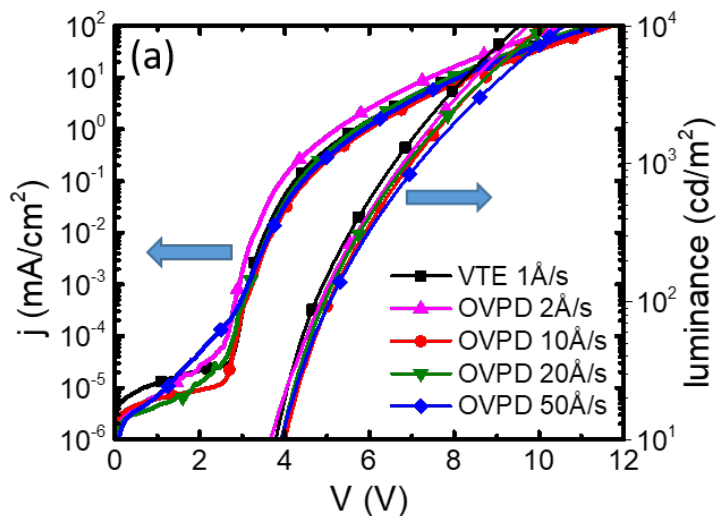
Increasing carrier gas flow rate

Crystals	Needle morph. Long, large	Flat morph. Uniaxial, small
Source temperature	Low	High
Substrate temperature	High	Low
Carrier gas flow rate	Low	High
Chamber pressure	Low	High

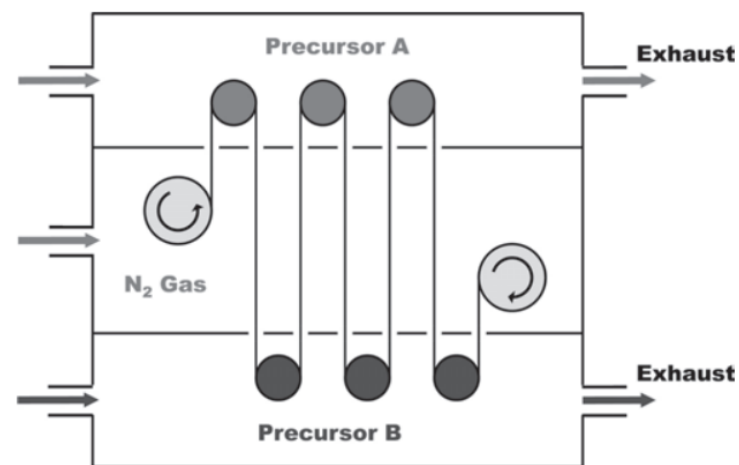
Increased Roll-Off at Highest Growth Rates



Heterogeneous Nucleation of Defects at High OVPD Growth Rates



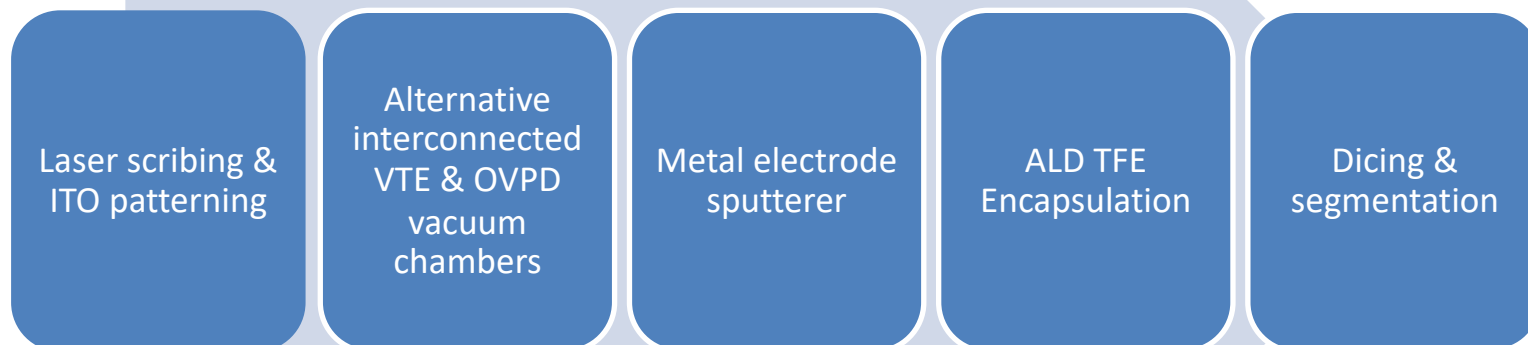
- Current OLED display encapsulation: CVD thin film encapsulation (TFE)
- Atomic layer deposition (ALD) advantages:
  - Pin-hole free layer
  - R2R compatible
  - Low WVTR  $< 2 \times 10^{-6}$  (Ref. E.G. Jeong, et al, Journal of Information Display, 2020)
- Approach at U of Michigan:
  - Test package: electrical Ca-test circuit covered by ALD-grown metal oxide TFEs
  - Test set-up: customized acrylic box with epoxy seal and controlled humidity
- Impact on cost analysis:
  - One or two additional vacuum chambers
  - Negligible material cost increase



Ref. S.M. George, et al, 2011 Society of Vacuum coaters, 2011.



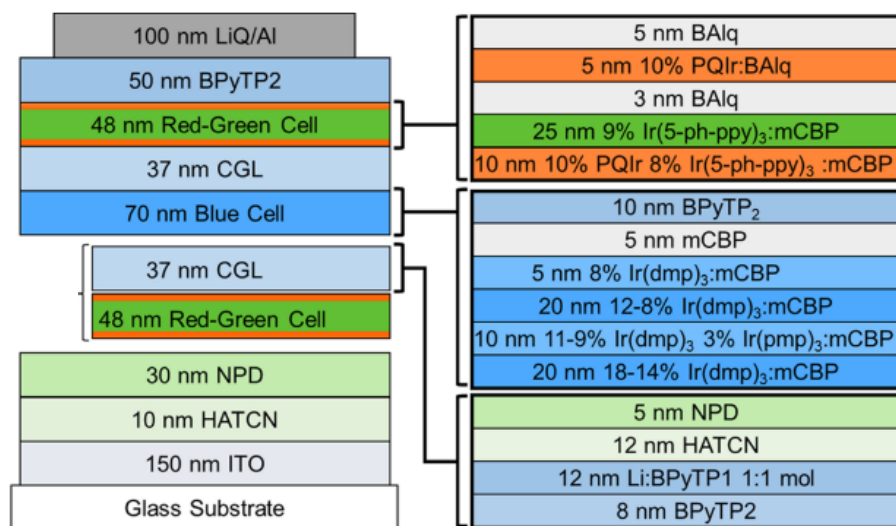
ITO coated plastic  
substrate rolls with  
outcoupling fixtures



Lighting panels

Target: \$10 /klm or \$100 /m<sup>2</sup> (lighting at 10 klm/m<sup>2</sup> )

## Reliable efficient WOLED structure design



- 3 R-G cells and 1 Blue cell
- CRI = 85.2, CCT = 2890 K
- EQE = 141% with outcoupling scheme
- LPE = 47.2 lm/W at 1000 nits.
- T70 = 50000 hr.
- Intensity: 200k cd/m<sup>2</sup>
- [CGL+ETL+HTL+cathode] in VTE
- [R-G-B EML] in OVPD
- 24 VTE subchambers + 10 OVPD subchambers (blends) + sputterer (Al)

Ref. Caleb Coburn, et al, ACS Photonics, 2018.5

Capacity	Unit	Base case
Rolling speed	m/hour	540
Roll prep / loading time	hour/hour	0.05
Substrate width	m	1.5
Campaign Length	Month	11
Maintenance Time	Month	1
Production per line	m <sup>2</sup> /machine/year	6094 k



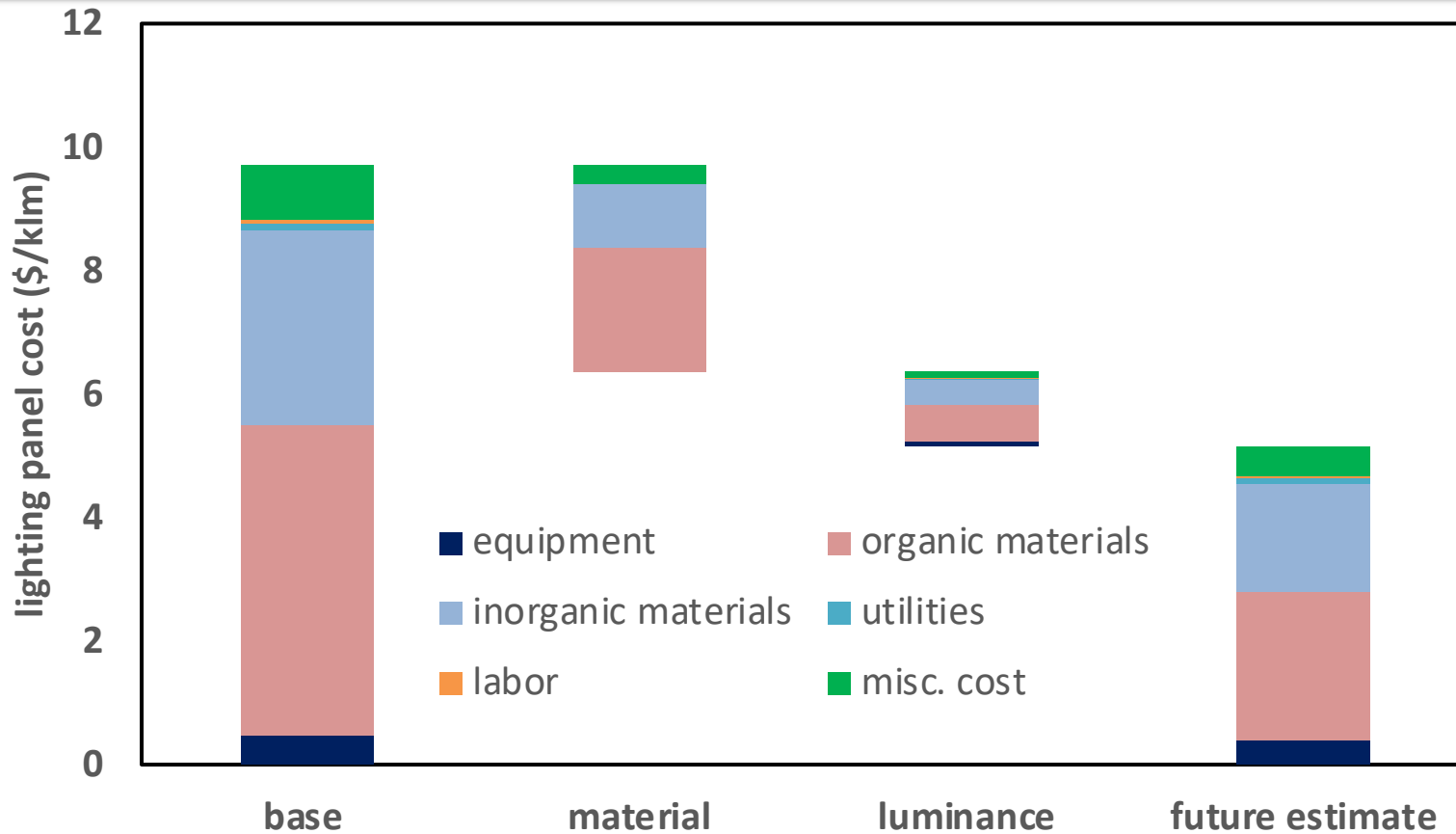
1.5 m-long growth window,  
5 nm/s rate, thickest  
organic layer 50nm  $\Rightarrow$  0.15  
m/s



5% prep/loading time



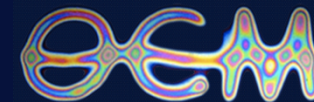
Uniform growth in Gen6  
chamber (R. Lunt, et al, APL,  
2009)



- 10% miscellaneous cost
- Material cost reduction
- 20% higher operation luminance compared to initial assumption (10000 lm/m<sup>2</sup>)
- Future estimate: \$5.2/klm



# Comparison with DoE metrics



	DoE 2019*	DoE 2025*	DoE 2035*	R2R
Capital cost (\$M)	50	200	400	293
Capacity(m <sup>2</sup> /yr)	25k	500k	2400k	6094k
Depreciation(\$/m <sup>2</sup> )	400	80	35	4.8
Organic cost(\$/m <sup>2</sup> )	200	80	35	50.2
Inorganic cost(\$/m <sup>2</sup> )	600	200	100	31.6
Labor(\$/m <sup>2</sup> )	100	15	5	0.5
Others(\$/m <sup>2</sup> )	50	10	5	1.1
Total unyielded(\$/m <sup>2</sup> )	1350	385	180	88.2
Yield (%)	70	80	90	90
Total(\$/m <sup>2</sup> )	1930	480	200	98

\* DoE EERE “2019 Lighting R&D Opportunities”, Table 3.9. Current status and cost targets for OLED panels produced by traditional methods.



- R2R Systems can combine multiple deposition technologies (including encapsulation) for efficient, high throughput manufacturing
- OVPD provides extraordinary control over morphology, doping concentration, device structure
- DOE cost targets for WOLEDs can be met using high volume R2R deposition

**Thanks to the DOE/EERE for support of this work**